Philips Compagents-Signetics

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Status	Product Specification				
Memory Products					

82S147 / 82S147A 急出货 4K-bit TTL bipolar PROM

DESCRIPTION

The 82S147 and 82S147A are field-programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The standard devices are supplied with all outputs at locical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

The 82S147 and 82S147A include on-chip decoding and one Chip Enable input for ease of memory expansion, and feature 3-State outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

The 82S147 and 82S147A devices are also processed to military requirements for operation over the military temperature range. For specifications and ordering information consult the Signetics Military Data Handbook.

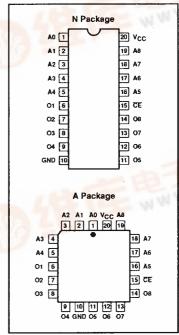
FEATURES

- · Address access time:
 - N82S147: 60ns max
 - N82S147A: 45ns max
- Power dissipation: 625mW/bit typ
- Input loading: -100μA max
- One Chip Enable input
- On-chip address decoding
- No separate fusing pins
- Fully TTL compatible
- Outputs: 3-State
- Unprogrammed outputs are Low level

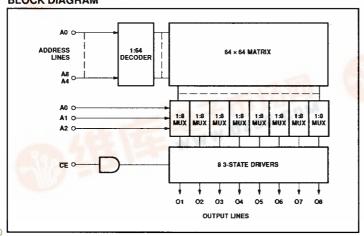
APPLICATIONS

- Prototyping/volume production
- Sequential controllers
- Microprogramming
- Hardwired algorithms
- Control store
- Random logic
- Code conversion

PIN CONFIGURATIONS



BLOCK DIAGRAM



4K-bit TTL bipolar PROM (512 \times 8)

82S147 / 82S147A

ORDERING INFORMATION

DESCRIPTION	ORDER CODE				
20-Pin Plastic Dual-In-Line 300mil-wide	N82S147 N, N82S147A N				
20-Pin Plastic Leaded Chip Carrier 350mil-square	N82S147 A, N82S147A A				

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT	
Vcc	Supply voltage	+7.0	V _{DC}	
V _{IN}	Input voltage	+5.5	V _{DC}	
Vo	Output voltage Off-State	+5.5	V _{DC}	
T _{amb}	Operating temperature range	0 to +75	%	
T _{sta}	Storage temperature range	-65 to +150	°C	

DC ELECTRICAL CHARACTERISTICS

 $0^{\circ}C \le T_{amb} \le +75^{\circ}C, 4.75V \le V_{CC} \le 5.25V$

		TEST CONDITIONS ^{1,2}		LIMITS			
SYMBOL	PARAMETER		Min	Typ ³	Max	UNIT	
Input volt	age						
V _{IL}	Low	-			0.8	V	
V_{IH}	High		2.0	ļ		V	
V _{IC}	Clamp	I _{IN} = -12mA		-0.8	-1.2	٧	
Output vo	Itage			•			
		CE = Low					
V_{OL}	Low	$I_{OUT} = 9.6mA$		1	0.45	V	
V _{OH}	High	$I_{OUT} = -2mA$	2.4			V	
Input curi	ent						
I _{IL}	Low	V _{IN} = 0.45V			-100	μА	
I _{IH}	High	$V_{IN} = 5.5V$		1	40	μΑ	
Output cu	rrent		.,				
loz	Hi-Z state	CE = High, V _{OUT} = 5.5V			40	μΑ	
		\overline{CE} = High, V_{OUT} = 0.5V			-40	μΑ	
los	Short circuit ⁴	$\overline{CE} = Low, V_{OUT} = 0V$	-15		-70	mA	
Supply co	urrent ⁵						
lcc		V _{CC} ≈ 5.25V		125	155	mA	
Capacita	nce						
		CE = High, V _{CC} = 5.0V					
CIN	Input	$V_{IN} = 2.0V$		5		pF	
Cour	Output	$V_{OUT} = 2.0V$		8		pF	

NOTES:

- 1. All voltages with respect to network ground.
- 2. Positive current is defined as into the terminal referenced.
- 3. Typical values are at $V_{CC} = 5V$, $T_{amb} = +25^{\circ}C$.
- 4. Duration of the short circuit should not exceed 1 second.
- 5. Measured with all inputs grounded and all outputs open.

4K-bit TTL bipolar PROM (512 \times 8)

82S147 / 82S147A

AC ELECTRICAL CHARACTERISTICS

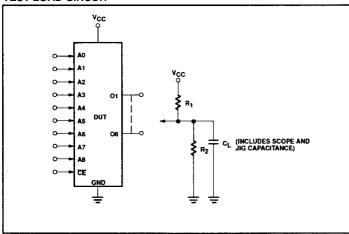
 $R_1 = 270\Omega$, $R_2 = 600\Omega$, $C_L = 30 pF$, $0^{\circ}C \le T_{amb} \le +75^{\circ}C$, $4.75V \le V_{CC} \le 5.25V$

SYMBOL PARAMETER		то	FROM	N82S147		N82S147A				
	PARAMETER			Min	Typ ¹	Max	Min	Typ ¹	Max	UNIT
Access tim	e ²									
t _{AA}		Output	Address		45	60		40	45	ns
tce		Output	Chip Enable		20	35		20	30	ns
Disable tim	ie ³									
tco		Output	Chip Disable		20	35		20	30	ns

NOTES:

- Typical values are at V_{CC} = 5V, T_{amb} = +25°C.
 Tested at an address cycle time of 1μs.
 Measured at a delta of 0.5V from Logic Level with R₁ = 750Ω, R₂ = 750Ω, C_L = 5pF.

TEST LOAD CIRCUIT



VOLTAGE WAVEFORMS

